Symposium Polarization Field Control in Group III-Nitrides (SYPN)

jointly organized by
the Semiconductor Physics Divsion (HL),
the Thin Films Division (DS), and
the Surface Physics Division (O)

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Overview of Invited Talks and Sessions

(lecture room H1)

Invited Talks

SYPN 1.1	Thu	9:30–10:00	H1	**Growth and applications of N-polar (Al,Ga,In)N** — •Stacia Keller, Umesh K Mishra
SYPN 1.2	Thu	10:00–10:30	H1	**Green light-emitting diodes and laser heterostructures on semi-polar GaN(11-22)/sapphire substrates** — •Andre Strittmatter
SYPN 1.3	Thu	10:30–11:00	H1	**Pros and cons of green InGaN lasers on polar GaN substrates** — •Uwe Strauss, Adrian Avramescu, Teresa Lermer, Jens Müller, Christoph Eichler, Stephan Lutgen
SYPN 1.4	Thu	11:15–11:45	H1	**Molecular beam epitaxy as a method for the growth of free-standing zinc-blende GaN layers and substrates.** — •Sergei Novikov, Thomas Foxon, Anthony Kent
SYPN 1.5	Thu	11:45–12:15	H1	**Three-dimensional GaN for semipolar light emitters** — •Thomas Wunderer, Frank Lipski, Stephan Schwaiger, Ferdinand Scholz, Martin Feneberg, Klaus Thonke, Andrey Chuvilin, Ute Kaiser, Sebastian Metzner, Frank Bertram, Jürgen Christen, Clemens Vierheilig, Ulrich Schwarz

Sessions

SYPN 1.1–1.5	Thu	9:30–12:15	H1	**Polarization Field Control in Group-III-Nitrides**